FW216A

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N-Channel Power MOSFET 35V, 4.5A, $64m\Omega$, Dual SOIC8

Features

- ON-resistance Nch : RDS(on)1=49m Ω (typ.)
- · 4.0V drive
- · Halogen free compliance
- · Protection diode in

Specifications

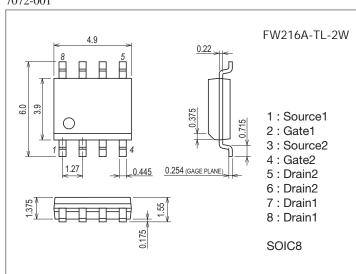
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V _{DSS}		35	V
Gate to Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		4.5	Α
Drain Current (PW≤10μs)	IDP	Duty cycle≤1%	18	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (2000mm²x0.8mm) 1unit, PW≤10s	1.6	W
Total Dissipation	PT	When mounted on ceramic substrate (2000mm ² x0.8mm), PW≤10s	2.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7072-001

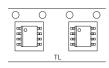


Product & Package Information

• Package : SOIC8

• JEITA, JEDEC : SC-87, SOT-96 • Minimum Packing Quantity : 2,500 pcs./reel

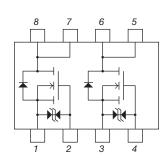
Packing Type: TL





Marking

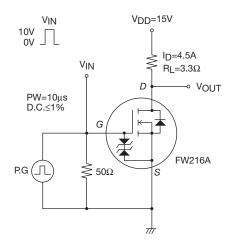
Electrical Connection



Electrical Characteristics at Ta=25°C

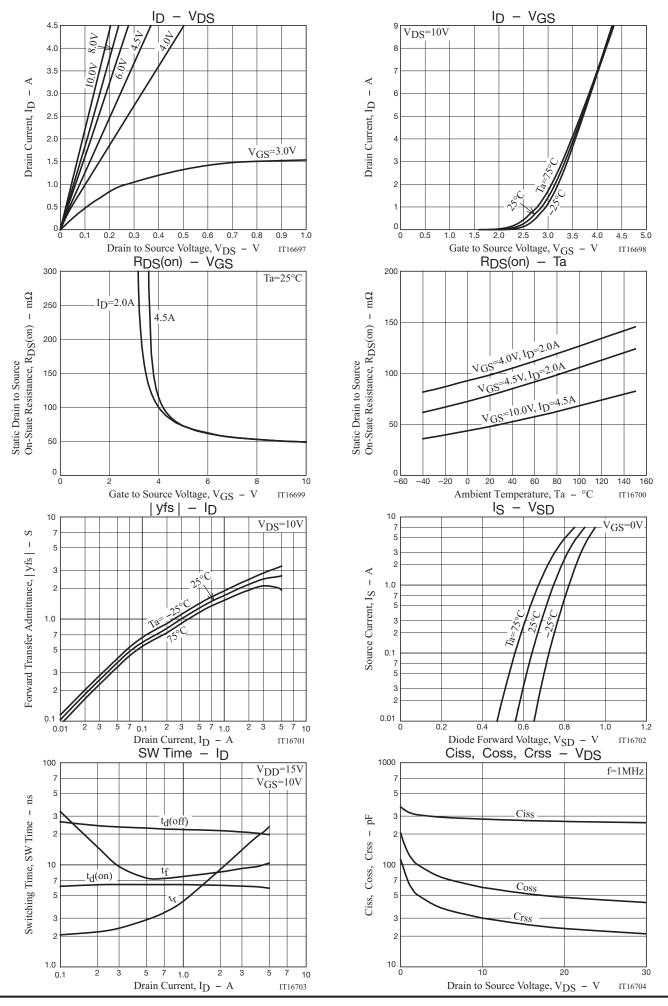
Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =35V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA 1.5			2.5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =4.5A		2.6		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =4.5A, V _{GS} =10V		49	64	mΩ
	R _{DS} (on)2	I _D =2A, V _{GS} =4.5V		80	112	mΩ
	R _{DS} (on)3	I _D =2A, V _{GS} =4.0V		100	140	mΩ
Input Capacitance	Ciss			280		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss			30		pF
Turn-ON Delay Time	t _d (on)			6		ns
Rise Time	t _r	Considered Total Circuit		21		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		20		ns
Fall Time	tf			10		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =4.5A		1.2		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.85	1.2	V

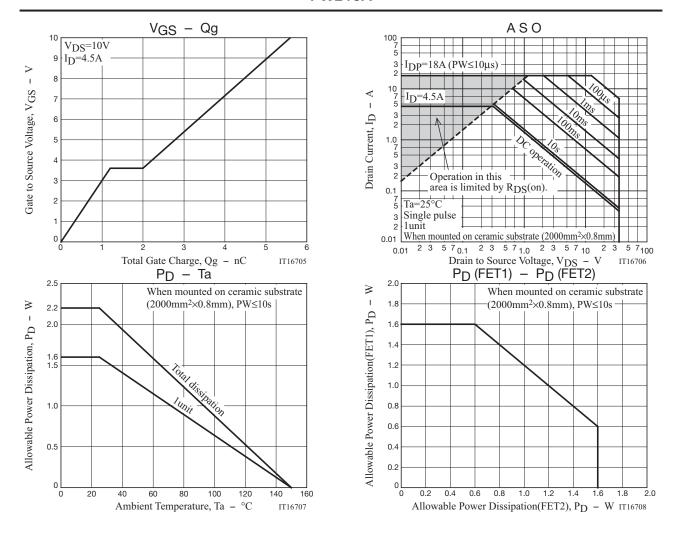
Switching Time Test Circuit



Ordering Information

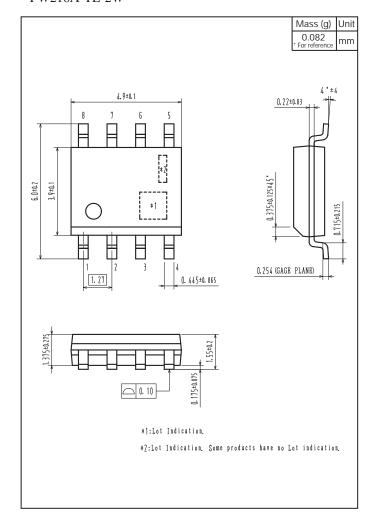
Device	Package	Shipping	memo	
FW216A-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free	

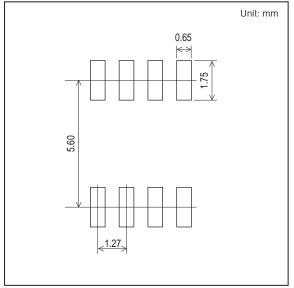




Outline Drawing FW216A-TL-2W

Land Pattern Example





Note on usage: Since the FW216A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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